Francesco La Via

List of Publications by Year in descending order

389 papers	4,562 citations	186265 28 h-index	206112 48 g-index
393 all docs	393 docs citations	393 times ranked	2344 citing authors

#	Article	IF	Citations
1	The development of a fully MRI-compatible silicon carbide neural interface. , 2022, , 161-195.		0
2	Effect of the Oxidation Process on Carrier Lifetime and on SF Defects of 4H SiC Thick Epilayer for Detection Applications. Micromachines, 2022, 13, 1042.	2.9	4
3	Impact of Nitrogen on the Selective Closure of Stacking Faults in 3C-SiC. Crystal Growth and Design, 2022, 22, 4996-5003.	3.0	6
4	Detector Response to D-D Neutrons and Stability Measurements with 4H Silicon Carbide Detectors. Materials, 2021, 14, 568.	2.9	4
5	Silicon Carbide and MRI: Towards Developing a MRI Safe Neural Interface. Micromachines, 2021, 12, 126.	2.9	10
6	Mechanism of stacking fault annihilation in 3C-SiC epitaxially grown on Si(001) by molecular dynamics simulations. CrystEngComm, 2021, 23, 1566-1571.	2.6	4
7	Epitaxial Growth and Characterization of 4H-SiC for Neutron Detection Applications. Materials, 2021, 14, 976.	2.9	11
8	Initial investigations into the MOS interface of freestanding 3C-SiC layers for device applications. Semiconductor Science and Technology, 2021, 36, 055006.	2.0	4
9	Growth of thick [1â€¯1â€¯1]-oriented 3C-SiC films on T-shaped Si micropillars. Materials and Design, 2021, 208, 109833.	7.0	9
10	Overgrowth of Protrusion Defects during Sublimation Growth of Cubic Silicon Carbide Using Free-Standing Cubic Silicon Carbide Substrates. Crystal Growth and Design, 2021, 21, 4046-4054.	3.0	6
11	A study on free-standing 3C-SiC bipolar power diodes. Applied Physics Letters, 2021, 118, .	3.3	3
12	Extended defects in 3C-SiC: Stacking faults, threading partial dislocations, and inverted domain boundaries. Acta Materialia, 2021, 213, 116915.	7.9	26
13	Effect of Nitrogen and Aluminum Doping on 3C-SiC Heteroepitaxial Layers Grown on 4Â° Off-Axis Si (100). Materials, 2021, 14, 4400.	2.9	10
14	Measurement of Residual Stress and Youngâ€™s Modulus on Micromachined Monocrystalline 3C-SiC Layers Grown on <111> and <100> Silicon. Micromachines, 2021, 12, 1072.	2.9	11
15	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. Materials, 2021, 14, 5348.	2.9	34
16	Characterization of protrusions and stacking faults in 3C-SiC grown by sublimation epitaxy using 3C-SiC-on-Si seeding layers. Advanced Materials Proceedings, 2021, 2, 774-778.	0.2	4
17	Status and Prospects of Cubic Silicon Carbide Power Electronics Device Technology. Materials, 2021, 14, 5831.	2.9	18
18	The NUMEN Technical Design Report. International Journal of Modern Physics A, 2021, 36, .	1.5	21

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19	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. Materialia, 2020, 9, 100528.	2.7	12
20	Recent results on heavy-ion direct reactions of interest for 0Î½Î²Î² decay at INFN - LNS. Journal of Physics: Conference Series, 2020, 1610, 012004.	0.4	0
21	The NUMEN Heavy Ion Multidetector for a Complementary Approach to the Neutrinoless Double Beta Decay. Universe, 2020, 6, 129.	2.5	26
22	Silicon Carbide characterization at the n_TOF spallation source with quasi-monoenergetic fast neutrons. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2020, 983, 164578.	1.6	5
23	Generation and Termination of Stacking Faults by Inverted Domain Boundaries in 3C-SiC. Crystal Growth and Design, 2020, 20, 3104-3111.	3.0	14
24	Silicon Carbide devices for radiation detection and measurements. Journal of Physics: Conference Series, 2020, 1561, 012013.	0.4	4
25	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. Advanced Electronic Materials, 2020, 6, 1901171.	5.1	25
26	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. Applied Physics Reviews, 2020, 7, 021402.	11.3	35
27	Editorial for the Special Issue on SiC Based Miniaturized Devices. Micromachines, 2020, 11, 405.	2.9	0
28	Characterization of 4H- and 6H-Like Stacking Faults in Cross Section of 3C-SiC Epitaxial Layer by Room-Temperature Î¼-Photoluminescence and Î¼-Raman Analysis. Materials, 2020, 13, 1837.	2.9	12
29	On the origin of the premature breakdown of thermal oxide on 3C-SiC probed by electrical scanning probe microscopy. Applied Surface Science, 2020, 526, 146656.	6.1	10
30	10.1063/1.5132300.1. , 2020, , .		0
31	Recent results on heavy-ion induced reactions of interest for neutrinoless double beta decay at INFN-LNS. Journal of Physics: Conference Series, 2020, 1643, 012074.	0.4	1
32	(Invited) Stacking Faults in 3C-SiC: From the Crystal Structure, to the Electrical Behavior. ECS Meeting Abstracts, 2020, MA2020-02, 1762-1762.	0.0	0
33	Biocompatibility between Silicon or Silicon Carbide surface and Neural Stem Cells. Scientific Reports, 2019, 9, 11540.	3.3	24
34	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. Materials, 2019, 12, 2179.	2.9	13
35	Limitations during Vapor Phase Growth of Bulk (100) 3C-SiC Using 3C-SiC-on-SiC Seeding Stacks. Materials, 2019, 12, 2353.	2.9	6
36	Fabrication of a Monolithic Implantable Neural Interface from Cubic Silicon Carbide. Micromachines, 2019, 10, 430.	2.9	25

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37	Recent results on Heavy-Ion induced reactions of interest for 0Î½Î²Î² decay. Journal of Physics: Conference Series, 2019, 1308, 012002.	0.4	0
38	Laser Annealing of P and Al Implanted 4H-SiC Epitaxial Layers. Materials, 2019, 12, 3362.	2.9	13
39	Temperature Investigation on 3C-SiC Homo-Epitaxy on Four-Inch Wafers. Materials, 2019, 12, 3293.	2.9	15
40	The NUMEN project @ LNS: Status and perspectives. AIP Conference Proceedings, 2019, , .	0.4	1
41	New experimental campaign of NUMEN project. AIP Conference Proceedings, 2019, , .	0.4	0
42	The NUMEN project @ LNS: Status and perspectives. AIP Conference Proceedings, 2019, , .	0.4	0
43	New thick silicon carbide detectors: Response to 14 MeV neutrons and comparison with single-crystal diamonds. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 946, 162637.	1.6	18
44	Growth and Coalescence of 3C-SiC on Si(111) Micro-Pillars by a Phase-Field Approach. Materials, 2019, 12, 3223.	2.9	9
45	Ohmic contacts on n-type and p-type cubic silicon carbide (3C-SiC) grown on silicon. Materials Science in Semiconductor Processing, 2019, 93, 295-298.	4.0	13
46	Nuclear fragment identification with <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll" id="d1e1454" altimg="si68.gif"><mml:mi>Î”</mml:mi></mml:math>E-E telescopes exploiting silicon carbide detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 925, 60-69.	1.6	14
47	3C-SiC grown on Si by using a Si1-xGex buffer layer. Journal of Crystal Growth, 2019, 519, 1-6.	1.5	9
48	Recent results on heavy-ion induced reactions of interest for neutrinoless double beta decay at INFN-LNS. EPJ Web of Conferences, 2019, 223, 01009.	0.3	0
49	Electrical Properties of Thermal Oxide on 3C-SiC Layers Grown on Silicon. Materials Science Forum, 2019, 963, 479-482.	0.3	2
50	3C-SiC Growth on Inverted Silicon Pyramids Patterned Substrate. Materials, 2019, 12, 3407.	2.9	12
51	Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates. Materials Science Forum, 2019, 963, 149-152.	0.3	2
52	Simulation of the Growth Kinetics in Group IV Compound Semiconductors. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800597.	1.8	6
53	X-ray diffraction on stacking faults in 3C-SiC epitaxial microcrystals grown on patterned Si(0â€¯0â€¯1) wafers. Journal of Crystal Growth, 2019, 507, 70-76.	1.5	6
54	New results from the NUMEN project. , 2019, , .		0

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55	From thin film to bulk 3C-SiC growth: Understanding the mechanism of defects reduction. Materials Science in Semiconductor Processing, 2018, 78, 57-68.	4.0	99
56	Measuring nuclear reaction cross sections to extract information on neutrinoless double beta decay. Journal of Physics: Conference Series, 2018, 966, 012021.	0.4	1
57	SiCILIAâ€"Silicon Carbide Detectors for Intense Luminosity Investigations and Applications. Sensors, 2018, 18, 2289.	3.8	51
58	Solving the critical thermal bowing in 3C-SiC/Si(111) by a tilting Si pillar architecture. Journal of Applied Physics, 2018, 123, 185703.	2.5	6
59	Silicon Carbide detectors for nuclear physics experiments at high beam luminosity. Journal of Physics: Conference Series, 2018, 1056, 012032.	0.4	3
60	The NUMEN project: NUclear Matrix Elements for Neutrinoless double beta decay. European Physical Journal A, 2018, 54, 1.	2.5	146
61	Protrusions reduction in 3C-SiC thin film on Si. Journal of Crystal Growth, 2018, 498, 248-257.	1.5	24
62	3C-SiÐ¡ Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiÐ¡ Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). Materials Science Forum, 2018, 924, 913-918.	0.3	12
63	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. Journal of Physical Chemistry C, 2017, 121, 4304-4311.	3.1	10
64	Electrical properties of extended defects in 4H-SiC investigated by photoinduced current measurements. Applied Physics Express, 2017, 10, 036601.	2.4	9
65	Carbonization and transition layer effects on 3C-SiC film residual stress. Journal of Crystal Growth, 2017, 473, 11-19.	1.5	22
66	Growing bulk-like 3C-SiC from seeding material produced by CVD. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600429.	1.8	2
67	Sublimation growth of bulk 3C-SiC using 3C-SiC-on-Si (1 0 0) seeding layers. Journal of Crystal Growth, 2017, 478, 159-162.	1.5	19
68	Photo-electrochemical water splitting in silicon based photocathodes enhanced by plasmonic/catalytic nanostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2017, 225, 128-133.	3.5	13
69	The NUMEN project @ LNS: Status and perspectives. AIP Conference Proceedings, 2017, , .	0.4	1
70	NURE: An ERC project to study nuclear reactions for neutrinoless double beta decay. , 2017, , .		6
71	NUMEN project @ LNS: Status and perspectives. , 2017, , .		0
72	High growth rate 3C-SiC growth: from hetero-epitaxy to homo-epitaxy. MRS Advances, 2016, 1, 3643-3647.	0.9	2

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73	Optimization of Ion Implantation processes for 4H-SiC DIMOSFET. MRS Advances, 2016, 1, 3673-3678.	0.9	2
74	Silicon carbide detectors study for NUMEN project. EPJ Web of Conferences, 2016, 117, 10006.	0.3	27
75	Electrical Properties of Defects in 4H-SiC Investigated by Photo-Induced-Currents Measurements. Materials Science Forum, 2016, 858, 380-383.	0.3	1
76	Structural and electronic transitions in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">G</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">b</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mi mathvariant="normal">	3.2	33
77	Voids-Free 3C-SiC/Si Interface for High Quality Epitaxial Layer. Materials Science Forum, 2016, 858, 159-162.	0.3	2
78	Hydrogen Flux Influence on Homo-Epitaxial 4H-SiC Doping Concentration Profile for High Power Application. Materials Science Forum, 2016, 858, 197-200.	0.3	2
79	The nuclear matrix elements of 0νÎ²Î² decay and the NUMEN project at INFN-LNS. Journal of Physics: Conference Series, 2016, 730, 012006.	0.4	1
80	Photocatalytical activity of amorphous hydrogenated TiO2 obtained by pulsed laser ablation in liquid. Materials Science in Semiconductor Processing, 2016, 42, 28-31.	4.0	23
81	Laser plasma monitored by silicon carbide detectors. Radiation Effects and Defects in Solids, 2015, 170, 303-324.	1.2	3
82	Correlations between Crystal Quality and Electrical Properties by Means of Simultaneous Photoluminescence and Photocurrent Analysis. Materials Science Forum, 2015, 821-823, 257-260.	0.3	0
83	Interface state density evaluation of high quality hetero-epitaxial 3Câ€“SiC(001) for high-power MOSFET applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 198, 14-19.	3.5	15
84	Epitaxial Growth on 150 mm 2Â° off Wafers. Materials Science Forum, 2015, 821-823, 157-160.	0.3	1
85	Monte Carlo Study of the early Growth Stages of 3C-SiC on Misoriented <11-20> and <1-100> 6H-SiC Substrates: Role of Step-Island Interaction. Materials Science Forum, 2015, 821-823, 201-204.	0.3	2
86	Electrical Properties Evaluation on High Quality Hetero-Epitaxial 3C-SiC(001) for MOSFET Applications. Materials Science Forum, 2015, 821-823, 773-776.	0.3	3
87	Hetero-Epitaxial Single Crystal 3C-SiC Opto-Mechanical Pressure Sensor. Materials Science Forum, 2015, 821-823, 902-905.	0.3	1
88	Study of the role of particle-particle dipole interaction in dielectrophoretic devices for biomarkers identification. Lecture Notes in Electrical Engineering, 2015, , 9-12.	0.4	3
89	Mechanisms of growth and defect properties of epitaxial SiC. Applied Physics Reviews, 2014, 1, 031301.	11.3	89
90	A novel micro-Raman technique to detect and characterize 4H-SiC stacking faults. Journal of Applied Physics, 2014, 116, .	2.5	11

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91	(Invited) Three-Dimensional Epitaxial Si_{1-X}Ge_x, Ge and SiC Crystals on Deeply Patterned Si Substrates. ECS Transactions, 2014, 64, 631-648.	0.5	14
92	Monte Carlo Study of the Early Growth Stages of 3C-SiC on Misoriented and 6H-Sic Substrates. Materials Science Forum, 2014, 778-780, 238-242.	0.3	2
93	Fracture property and quantitative strain evaluation of hetero-epitaxial single crystal 3C-SiC membrane. Materials Research Express, 2014, 1, 015912.	1.6	4
94	Electrically Trimmable Phase Change Ge₂Sb₂Te₅ Resistors With Tunable Temperature Coefficient of Resistance. IEEE Transactions on Electron Devices, 2014, 61, 2879-2885.	3.0	3
95	Theoretical and experimental study of the role of cell-cell dipole interaction in dielectrophoretic devices: application to polynomial electrodes. BioMedical Engineering OnLine, 2014, 13, 71.	2.7	18
96	Evaluation of 3C-SiC/Si residual stress and curvatures along different wafer direction. Materials Letters, 2014, 118, 130-133.	2.6	8
97	MeV ion beams generated by intense pulsed laser monitored by Silicon Carbide detectors. Journal of Physics: Conference Series, 2014, 508, 012009.	0.4	3
98	Strain Evaluation and Fracture Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared Membrane. Materials Science Forum, 2014, 806, 11-14.	0.3	0
99	Monte Carlo study of the early growth stages of 3C-SiC on misoriented <11-20> and <1-100> 6H-SiC substrates: role of step-island interaction. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1606-1610.	0.8	0
100	Fast Growth Rate Epitaxy by Chloride Precursors. Materials Science Forum, 2013, 740-742, 167-172.	0.3	5
101	Microâ€Raman analysis and finiteâ€element modeling of 3â€‰Câ€SiC microstructures. Journal of Raman Spectroscopy, 2013, 44, 299-306.	2.5	12
102	Effects of Al Ion Implantation on 3C-SiC Crystal Structure. Materials Science Forum, 2013, 740-742, 613-616.	0.3	0
103	Patterned substrate with inverted silicon pyramids for 3Câ€“SiC epitaxial growth: A comparison with conventional (001) Si substrate. Journal of Materials Research, 2013, 28, 94-103.	2.6	14
104	Post-Growth Process Effect on Hetero-Epitaxial 3C-SiC Wafer Bow and Residual Stress. Materials Science Forum, 2013, 740-742, 301-305.	0.3	1
105	High performance SiC detectors for MeV ion beams generated by intense pulsed laser plasmas. Journal of Materials Research, 2013, 28, 87-93.	2.6	64
106	Stress nature investigation on heteroepitaxial 3Câ€“SiC film on (100) Si substrates. Journal of Materials Research, 2013, 28, 129-135.	2.6	6
107	Correlation between macroscopic and microscopic stress fields: Application to the 3Câ€“SiC/Si heteroepitaxy. Journal of Materials Research, 2013, 28, 104-112.	2.6	5
108	Introduction to Silicon Carbide â€” Materials, Processing and Devices â€“ ADDENDUM. Journal of Materials Research, 2013, 28, 786-786.	2.6	1

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109	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. Materials Science Forum, 2012, 717-720, 113-116.	0.3	2
110	Micro-Raman Analysis of a Micromachined 3C-SiC Cantilever. Materials Science Forum, 2012, 717-720, 525-528.	0.3	1
111	Stress Evaluation on Hetero-Epitaxial 3C-SiC Film on (100) Si Substrates. Materials Science Forum, 2012, 717-720, 521-524.	0.3	3
112	Consideration on the Thermal Expansion of 3C-SiC Epitaxial Layer on Si Substrates. Materials Science Forum, 2012, 711, 31-34.	0.3	1
113	Electron backscattering from stacking faults in SiC by means ofab initioquantum transport calculations. Physical Review B, 2012, 85, .	3.2	31
114	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. Materials Science Forum, 2012, 717-720, 149-152.	0.3	2
115	SiC Films and Coatings. , 2012, , 17-61.		15
116	Strain Field Analysis of 3C-SiC Free-Standing Microstructures by Micro-Raman and Theoretical Modelling. Materials Science Forum, 2012, 711, 55-60.	0.3	3
117	Growth and processing of heteroepitaxial 3C-SiC films for electronic devices applications. Materials Research Society Symposia Proceedings, 2012, 1433, 25.	0.1	2
118	Wafer Cut Effect on Hetero-Epitaxial 3C-SiC Film for MEMS Application. Electrochemical and Solid-State Letters, 2012, 15, H182.	2.2	6
119	Stress fields analysis in 3Câ€“SiC free-standing microstructures by micro-Raman spectroscopy. Thin Solid Films, 2012, 522, 20-22.	1.8	14
120	Large area optical characterization of 3 and 4 inches 4Hâ€“SiC wafers. Thin Solid Films, 2012, 522, 30-32.	1.8	4
121	Study of microstructure deflections and film/substrate curvature under generalized stress fields and mechanical properties. Thin Solid Films, 2012, 522, 26-29.	1.8	7
122	Crystal recovery from Alâ€implantation induced damaging in 3Câ€SiC films. Physica Status Solidi - Rapid Research Letters, 2012, 6, 226-228.	2.4	2
123	Morphology and distribution of carbon nanostructures in a deposit produced by arc discharge in liquid nitrogen. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1005-1008.	2.7	4
124	Advanced Residual Stress Analysis and FEM Simulation on Heteroepitaxial 3Câ€“SiC for MEMS Application. Journal of Microelectromechanical Systems, 2011, 20, 745-752.	2.5	49
125	Study of the connection between stacking faults evolution and step kinetics in misoriented 4H-SiC epitaxial growths. Surface Science, 2011, 605, L67-L69.	1.9	9
126	Structural and electronic characterization of (2,33) bar-shaped stacking fault in 4H-SiC epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	21

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127	First Principles Investigation on the Modifications of the 4H-SiC Band Structure Due to the (4,4) and (3,5) Stacking Faults. Applied Physics Express, 2011, 4, 025802.	2.4	22
128	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. Electrochemical and Solid-State Letters, 2011, 14, H457.	2.2	0
129	Raman Stress Characterization of Hetero-Epitaxial 3C-SiC Free Standing Structures. Materials Science Forum, 2011, 679-680, 141-144.	0.3	7
130	Evolution of Extended Defects during Epitaxial Growths: A Monte Carlo Study. Materials Science Forum, 2011, 679-680, 48-54.	0.3	1
131	Publisherâ€™s Note: Defect Influence on Heteroepitaxial 3C-SiC Youngâ€™s Modulus [Electrochem. Solid-State Lett., 14, H161 (2011)]. Electrochemical and Solid-State Letters, 2011, 14, S3.	2.2	4
132	Complete Determination of the Local Stress Field in Epitaxial Thin Films Using Single Microstructure. Materials Science Forum, 2011, 679-680, 213-216.	0.3	10
133	Advanced Stress Analysis by Micro-Structures Realization on High Quality Hetero-Epitaxial 3C-SiC for MEMS Application. Materials Science Forum, 2011, 679-680, 133-136.	0.3	7
134	Defect Influence on Heteroepitaxial 3C-SiC Youngâ€™s Modulus. Electrochemical and Solid-State Letters, 2011, 14, H161.	2.2	39
135	3C-SiC Film Growth on Si Substrates. ECS Transactions, 2011, 35, 99-116.	0.5	32
136	Advanced Residual Stress Analysis on the Heteroepitaxial Growth of 3C-SiC/Si for MEMS Application. ECS Transactions, 2011, 35, 123-131.	0.5	1
137	High Power Density UV Optical Stress for Quality Evaluation of 4H-SiC Epitaxial Layers. ECS Transactions, 2011, 35, 117-122.	0.5	0
138	(Invited) High Quality 3C-SiC for MOS Applications. ECS Transactions, 2011, 41, 273-282.	0.5	3
139	Multiscale simulation for epitaxial silicon carbide growth by chlorides route. Thin Solid Films, 2010, 518, S6-S11.	1.8	3
140	Extended study of the step-bunching mechanism during the homoepitaxial growth of SiC. Thin Solid Films, 2010, 518, S159-S161.	1.8	22
141	High-quality 6inch (111) 3C-SiC films grown on off-axis (111) Si substrates. Thin Solid Films, 2010, 518, S165-S169.	1.8	61
142	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. Surface Science, 2010, 604, 939-942.	1.9	17
143	Study of the Evolution of Basal Plane Dislocations during Epitaxial Growth: Role of the Surface Kinetics. Materials Science Forum, 2010, 645-648, 539-542.	0.3	8
144	Bow in 6 Inch High-Quality Off-Axis (111) 3C-SiC Films. Materials Science Forum, 2010, 645-648, 167-170.	0.3	2

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145	Systematic first principles calculations of the effects of stacking faults defects on the 4H-SiC band structure. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	1
146	Single Shockley Faults Evolution Under UV Optical Pumping. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	3
147	Evolution of Stacking Faults Defects During Epitaxial Growths: Role of Surface Kinetics. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	0
148	Microtwin reduction in 3Câ€“SiC heteroepitaxy. Applied Physics Letters, 2010, 97, .	3.3	14
149	Optical investigation of bulk electron mobility in 3Câ€“SiC films on Si substrates. Applied Physics Letters, 2010, 97, 142103.	3.3	11
150	Optical characterization of bulk mobility in 3C-SiC films grown on different orientation of Si substrates. , 2010, , .		0
151	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. Journal of the Electrochemical Society, 2010, 157, H438.	2.9	20
152	Monte Carlo study of morphological surface instabilities during misoriented epitaxial growth of cubic and hexagonal polytypes. AIP Conference Proceedings, 2010, , .	0.4	2
153	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. Applied Physics Letters, 2009, 95, 111905.	3.3	24
154	Heteroepitaxy of 3C-SiC on different on-axis oriented silicon substrates. Journal of Applied Physics, 2009, 105, .	2.5	58
155	Residual Stress Measurement on Hetero-Epitaxial 3C-SiC Films. Materials Science Forum, 2009, 615-617, 629-632.	0.3	1
156	Extended Study of the Step-Bunching Mechanism during the Homoepitaxial Growth of SiC. Materials Science Forum, 2009, 615-617, 117-120.	0.3	2
157	Monte Carlo study of the step flow to island nucleation transition for close packed structures. Surface Science, 2009, 603, 2226-2229.	1.9	15
158	Effect of the miscut direction in (111) 3C-SiC film growth on off-axis (111)Si. Applied Physics Letters, 2009, 94, 101907.	3.3	27
159	Structural defects in (100) 3C-SiC heteroepitaxy: Influence of the buffer layer morphology on generation and propagation of stacking faults and microtwins. Diamond and Related Materials, 2009, 18, 1440-1449.	3.9	46
160	Low temperature reaction of point defects in ion irradiated 4Hâ€“SiC. Diamond and Related Materials, 2009, 18, 39-42.	3.9	4
161	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. Journal of Crystal Growth, 2008, 310, 971-975.	1.5	29
162	4H-SiC epitaxial layer growth by trichlorosilane (TCS). Journal of Crystal Growth, 2008, 311, 107-113.	1.5	65

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163	Heteroepitaxial growth of (111) 3C-SiC on (110) Si substrate by second order twins. Applied Physics Letters, 2008, 92, 224102.	3.3	20
164	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. Materials Science Forum, 2008, 600-603, 135-138.	0.3	16
165	Thin SiC-4H Epitaxial Layer Growth by Trichlorosilane (TCS) as Silicon Precursor with Very Abrupt Junctions. Materials Science Forum, 2008, 600-603, 127-130.	0.3	6
166	Compensation Effects in 7 MeV C Irradiated n-Doped 4H-SiC. Materials Science Forum, 2008, 600-603, 619-622.	0.3	3
167	Electrical properties of high energy ion irradiated 4H-SiC Schottky diodes. Journal of Applied Physics, 2008, 104, .	2.5	27
168	Effect of Mo interlayer on thermal stability of polycrystalline NiSi thin films. Journal of Applied Physics, 2007, 101, 063544.	2.5	1
169	Optical and electrical properties of 4H-SiC epitaxial layer grown with HCl addition. Journal of Applied Physics, 2007, 102, 043523.	2.5	17
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